74HC153; 74HCT153 Dual 4-input multiplexer Rev. 4 – 28 November 2013

1. General description

The 74HC153; 74HCT153 is a dual 4-input multiplexer. The device features independent enable inputs (nE) and common data select inputs (S0 and S1). For each multiplexer, the select inputs select one of the four binary inputs and routes it to the multiplexer output (nY). A HIGH on E forces the corresponding multiplexer outputs LOW. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

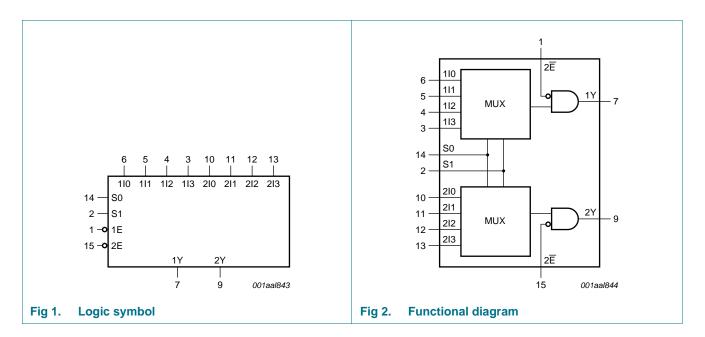
- Input levels:
 - For 74HC153: CMOS level
 - For 74HCT153: TTL level
- Non-inverting outputs
- Separate enable input for each output
- Common select inputs
- Complies with JEDEC standard no. 7A
- Permits multiplexing from n lines to 1 line
- Enable line provided for cascading (n lines to 1 line)
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.



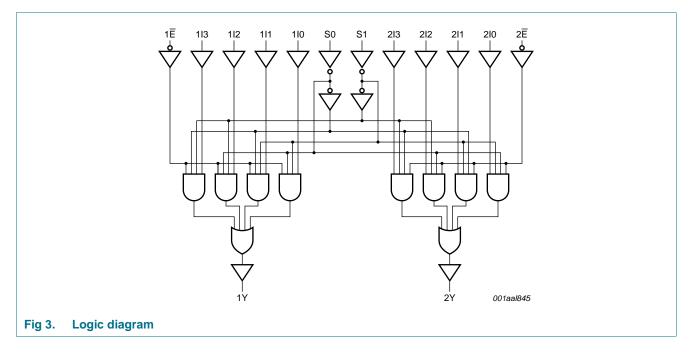
3. Ordering information

Table 1. Ordering information										
Type number	Package									
	Temperature range	Name	Description	Version						
74HC153N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1						
74HCT153N										
74HC153D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1						
74HCT153D			3.9 mm							
74HC153DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1						
74HCT153DB			width 5.3 mm							
74HC153PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1						
74HCT153PW			body width 4.4 mm							

4. Functional diagram

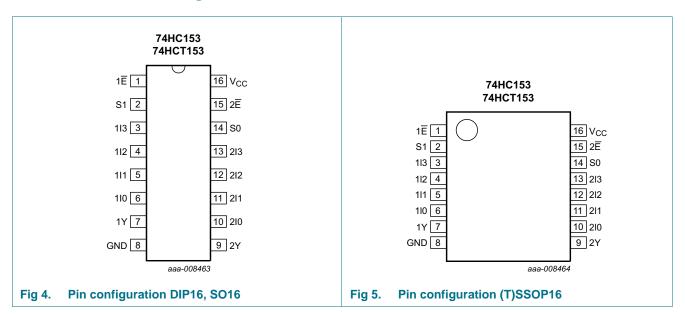


Dual 4-input multiplexer



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin dese	cription	
Symbol	Pin	Description
$1\overline{E}, 2\overline{E}$	1, 15	output enable inputs (active LOW)
S0, S1	14, 2	data select inputs
110, 111, 112, 113	6, 5, 4, 3	data inputs source 1
1Y	7	multiplexer output source 1
GND	8	ground (0 V)
2Y	9	multiplexer output source 2
210, 211, 212, 213	10, 11, 12, 13	data inputs source 2
V _{CC}	16	supply voltage

6. Functional description

Table 3.Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care.

select Inpu	ts	data inpu	uts			output enable	output
S0	S1	nl0	nl1	nl2	nl3	nE	nY
Х	Х	Х	Х	Х	x	Н	L
L	L	L	Х	Х	Х	L	L
L	L	Н	Х	Х	Х	L	Н
Н	L	Х	L	Х	Х	L	L
Н	L	Х	Н	Х	Х	L	Н
L	Н	Х	Х	L	Х	L	L
L	Н	Х	Х	Н	Х	L	Н
Н	Н	Х	Х	Х	L	L	L
Н	Н	Х	Х	Х	Н	L	Н

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					-
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{\rm I}$ < –0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	[1] _	±20	mA
I _{OK}	output clamping current	V_{O} < –0.5 V or V_{O} > V_{CC} + 0.5 V	[1] _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation		[2]		
	DIP16 package		-	750	mW
	SO16 and (T)SSOP16 packages		-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C. For (T)SSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC ²	153		74HC	74HCT153			
			Min	Тур	Max	Min	Тур	Max		
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V	
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V	
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C	
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V	
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V	
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V	

9. Static characteristics

Table 6.Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	ol Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	Min	Max	
74HC1	53									
V _{IH} HIGH-level input voltage	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V	
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
i	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to +125 °C		Un
			Min	Тур	Мах	Min	Max	Min	Max	
/ _{он}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = -20 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = -20 μ A; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
/ _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = 20 μ A; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1	-	±1	μA
СС	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 6.0 \ V \end{array}$	-	-	8.0	-	80	-	160	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	53									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
VIL	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
√ _{ОН}	HIGH-level	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 V$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
/ _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_0 = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μA
СС	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 5.5$ V	-	-	8	-	80	-	160	μA
∆I _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V								
		1ln, 2ln	-	45	162	-	203	-	221	μA
		nE	-	60	216	-	270	-	294	μA
		Sn	-	135	486	-	608	-	662	μA
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC153											
t _{pd}	propagation delay	1In to nY, 2In to nY; see <u>Figure 6</u>	<u>[1]</u>								
		$V_{CC} = 2.0 V$		-	47	145	-	180	-	220	ns
		$V_{CC} = 4.5 V$		-	17	29	-	36	-	44	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	14	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	14	25	-	31	-	38	ns
		Sn to nY; see Figure 7									
		$V_{CC} = 2.0 V$		-	50	150	-	190	-	225	ns
		$V_{CC} = 4.5 V$		-	18	30	-	38	-	45	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	15	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	14	26	-	33	-	38	ns
		nE to nY; see Figure 7									
		$V_{CC} = 2.0 V$		-	33	100	-	125	-	150	ns
		$V_{CC} = 4.5 V$		-	12	20	-	25	-	30	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	-	-	ns
		$V_{CC} = 6.0 V$		-	10	17	-	21	-	26	ns
t _t	transition time	see Figure 6	[2]								
		$V_{CC} = 2.0 V$		-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5 V$		-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0 V$		-	6	13	-	16	-	19	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC}	<u>[3]</u>	-	30	-	-	-	-	-	pF
74HCT15	53										
t _{PHL}	HIGH to LOW propagation	1In to nY, 2In to nY; see Figure 6	[1]								
	delay	$V_{CC} = 4.5 V$		-	19	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	16	-	-	-	-	-	ns
t _{PLH}	LOW to HIGH propagation	1In to nY, 2In to nY; see <u>Figure 6</u>	<u>[1]</u>								
	delay	$V_{CC} = 4.5 V$		-	13	24	-	30	-	36	ns
		$V_{CC} = 5.0 \text{ V}; C_{L} = 15 \text{ pF}$		-	16	-	-	-	-	-	ns

Table 7. Dynamic characteristics ...continued

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF; for test circuit, see Figure 8; unless otherwise specified

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
t _{pd}	propagation	Sn to nY; see Figure 7	[1]								
	delay	$V_{CC} = 4.5 V$		-	20	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	17	-	-	-	-	-	ns
		nE to nY; see Figure 7	[1]								
		$V_{CC} = 4.5 V$		-	14	27	-	34	-	41	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	11	-	-	-	-	-	ns
tt	transition time	see Figure 6	[2]								
		$V_{CC} = 4.5 V$		-	7	15	-	19	-	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} $-$ 1.5 V	<u>[3]</u>	-	30	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

 $\label{eq:ttilde} [2] \quad t_t \mbox{ is the same as } t_{THL} \mbox{ and } t_{TLH}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

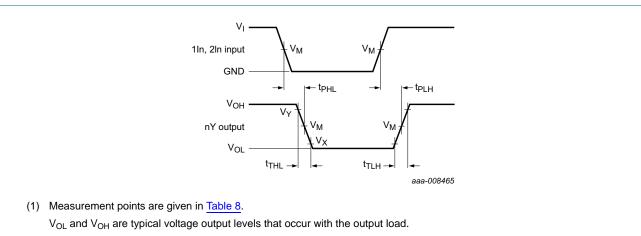


Fig 6. Waveforms showing the input (1In, 2In) to output (1Y, 2Y) propagation delays and output transition times

Table 8.	Measurement points	
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Туре	Input	Output		
	V _M	V _M	V _X	V _Y
74HC153	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}
74HCT153	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}

Dual 4-input multiplexer

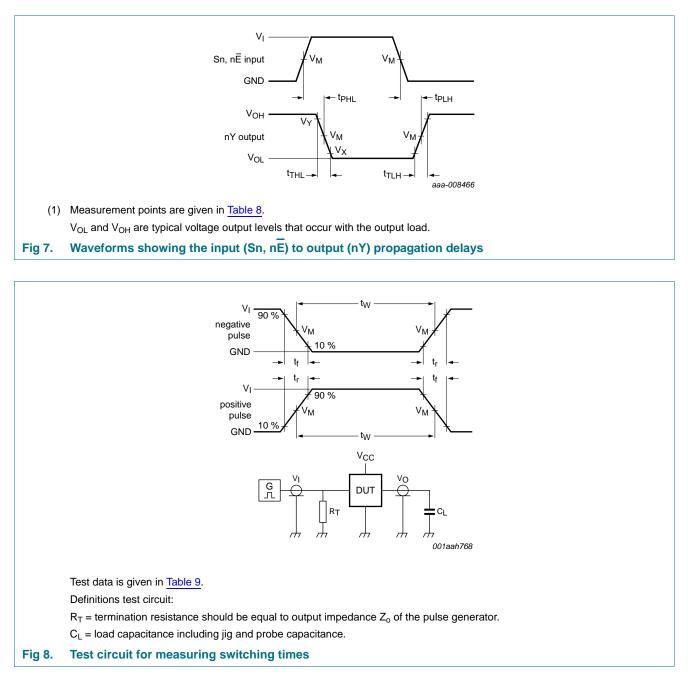


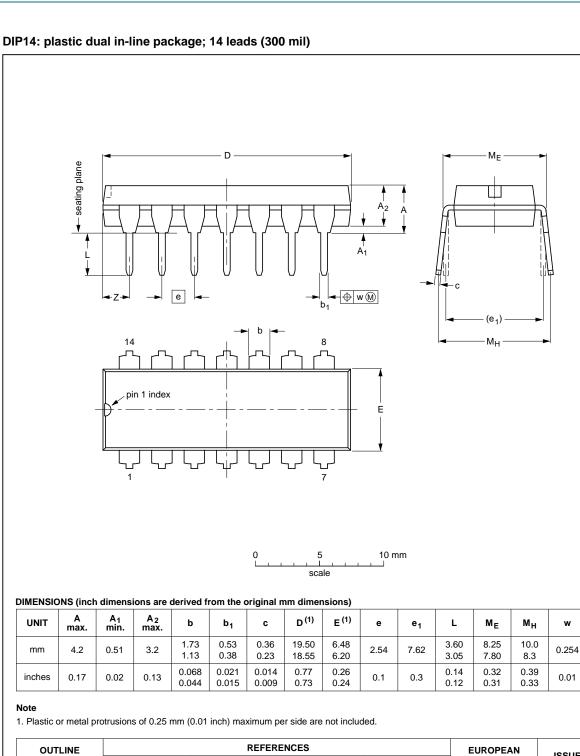
Table 9. Test data				
Туре	Input	Input		Test
	VI	t _r , t _f	CL	
74HC153	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT153	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

74HC HCT153

Dual 4-input multiplexer

SOT27-1

11. Package outline



OUTLINE		REFERENCES			EUROPEAN ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT27-1	050G04	MO-001	SC-501-14		$\square \bigcirc$	-99-12-27 03-02-13

Package outline SOT27-1 (DIP14) Fig 9.

74HC_HCT153

z⁽¹⁾

max.

2.2

0.087

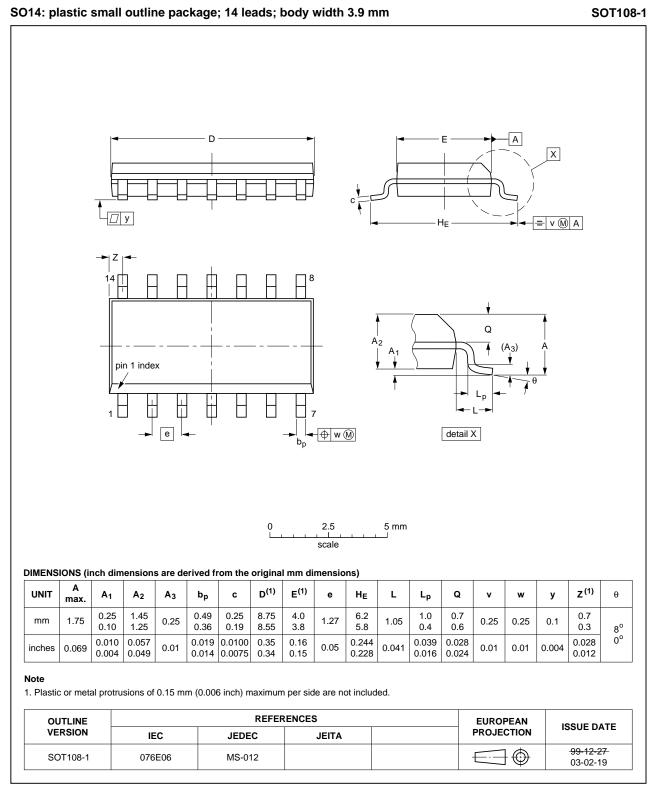


Fig 10. Package outline SOT108-1 (SO14)

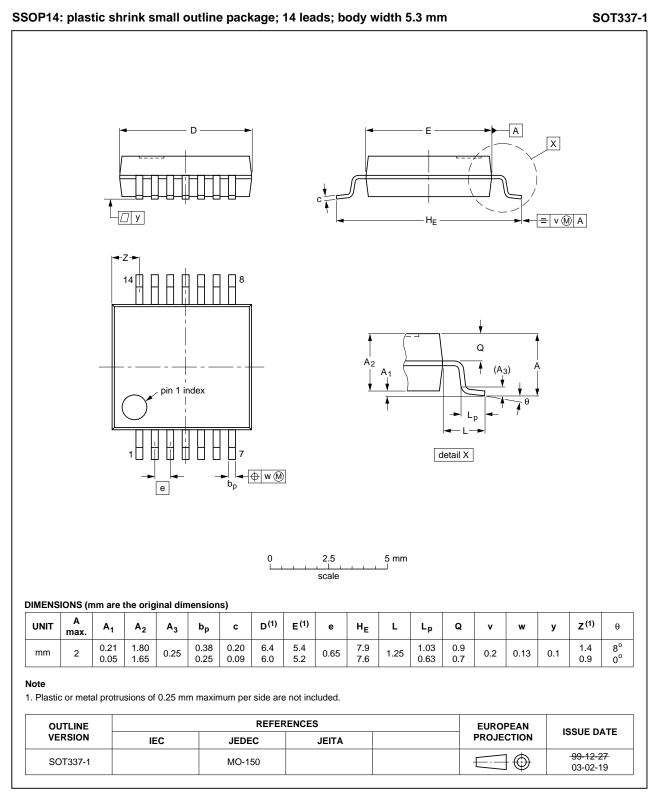


Fig 11. Package outline SOT337-1 (SSOP14)

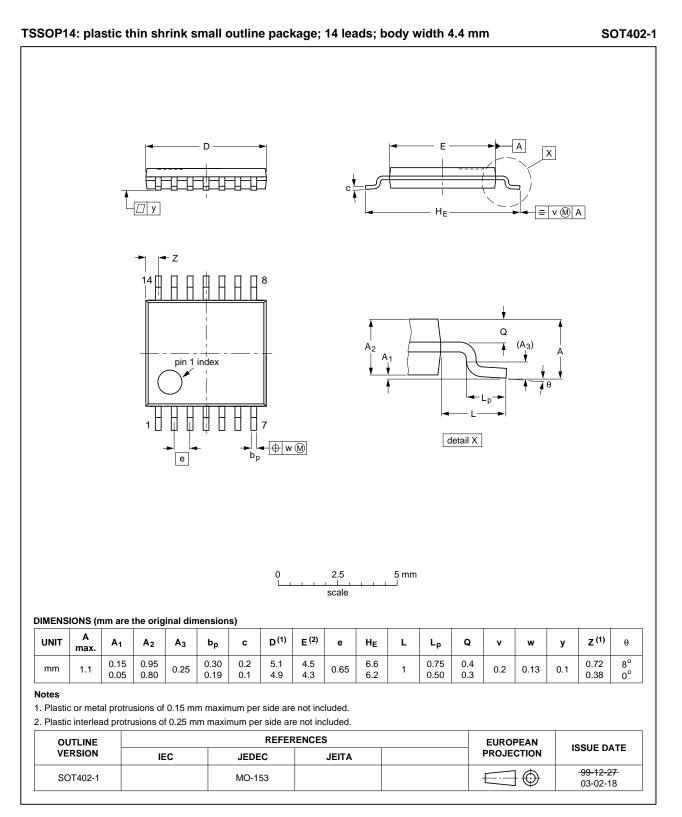


Fig 12. Package outline SOT402-1 (TSSOP14)

12. Abbreviations

Table 10. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal-Oxide Semiconductor			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
LSTTL	Low-power Schottky Transistor-Transistor Logic			
MM	Machine Model			
TTL	Transistor-Transistor Logic			

13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT153 v.4	20131128	Product data sheet	-	74HC_HCT153 v.3
Modifications:	 Figure 4 rem 	noved from the data sheet.		
74HC_HCT153 v.3	20130722	Product data sheet	-	74HC_HCT153_CNV v.2
74HC_HCT153_CNV v.2	19970827	Product specification	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Dual 4-input multiplexer

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